

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

**TD62476P, TD62477P, TD62478P, TD62479P****2CH PERIPHERAL AND / NAND / OR / NOR DRIVERS**

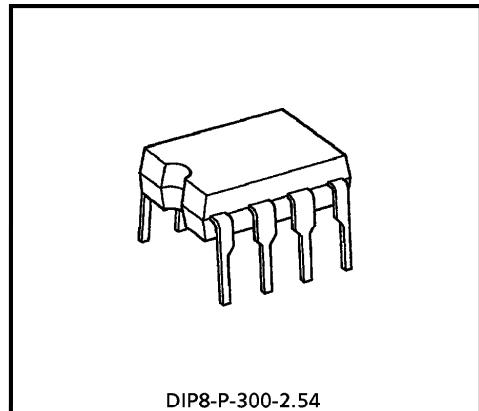
The TD62476P, TD62477P, TD62478P, TD62479P are comprised of two NPN single output stages and control inputs which can gate the outputs.

All units feature integral clamp diodes for switching inductive loads.

Applications include relay, hammer, lamp and display (LED) drivers.

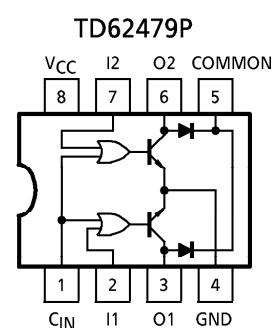
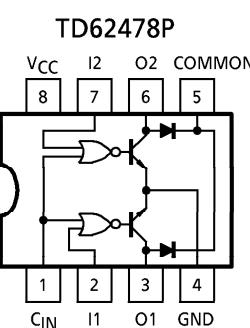
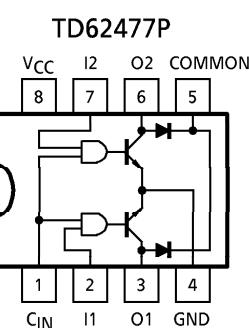
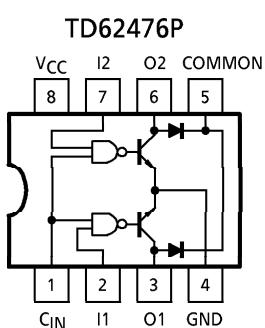
**FEATURES**

- Output current (single output) 350mA (Max.)
- High sustaining voltage output 35V (Min.)
- Output clamp diodes
- Inputs compatible with TTL and 5V CMOS
- Standard supply voltage
- Package type-P : DIP-8 pin



Weight : 0.45g (Typ.)

TD62476P		TD62477P		TD62478P		TD62479P					
INPUT		OUTPUT	INPUT		OUTPUT	INPUT		OUTPUT	INPUT		OUTPUT
C <sub>IN</sub>	I		C <sub>IN</sub>	I		C <sub>IN</sub>	I		C <sub>IN</sub>	I	
0	0	ON	0	0	OFF	0	0	ON	0	0	OFF
0	1	OFF	0	1	OFF	0	1	OFF	0	1	ON
1	0	OFF	1	0	OFF	1	0	OFF	1	0	ON
1	1	OFF	1	1	ON	1	1	OFF	1	1	ON

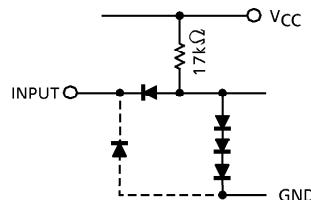
**PIN CONNECTION (TOP VIEW)**

961001EBA2

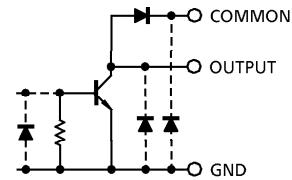
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**EQUIVALENT OF INPUTS AND OUTPUTS**

Equivalent of inputs



Equivalent of outputs



(Note) The input and output parasitic diodes cannot be used as clamp diodes.

**MAXIMUM RATINGS (Ta = 25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V <sub>CC</sub>	-0.5~7.0	V
Input Voltage	V <sub>IN</sub>	-0.5~5.5	V
Output Sustaining Voltage	V <sub>CE</sub> (SUS)	-0.5~35	V
Output Current	I <sub>OUT</sub>	350	mA / ch
Clamp Diode Reverse Voltage	V <sub>R</sub>	35	V
Clamp Diode Forward Current	I <sub>F</sub>	300	mA
Power Dissipation	P <sub>D</sub> (Note)	0.9	W
Operating Temperature	T <sub>opr</sub>	-30~75	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C

(Note) Delated above 25°C in the proportion of 7.2mW / °C.

**RECOMMENDED OPERATING CONDITIONS (Ta = -30~75°C)**

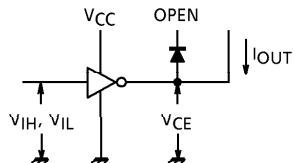
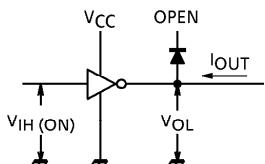
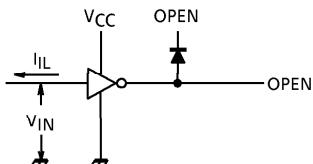
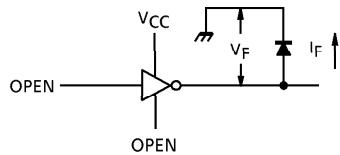
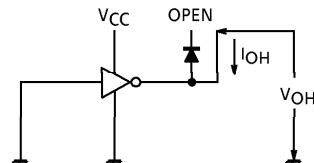
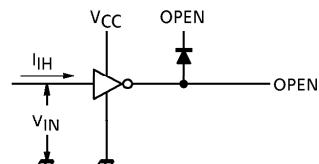
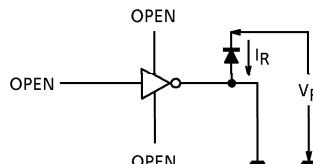
CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V <sub>CC</sub>	—	4.5	5.0	5.5	V
Output Sustaining Voltage	V <sub>CE</sub> (SUS)	—	0	—	35	V
Output Current	I <sub>OUT</sub>	DC 1 Circuit	0	—	300	mA / ch
		DC 2 Circuits	0	—	200	
Input Voltage	V <sub>IN</sub>	—	4.5	—	V <sub>CC</sub>	V
Clamp Diode Reverse Voltage	V <sub>R</sub>	—	—	—	35	V
Clamp Diode Forward Current	I <sub>F</sub>	—	—	—	300	mA
Power Dissipation	P <sub>D</sub>	—	—	—	0.4	W

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

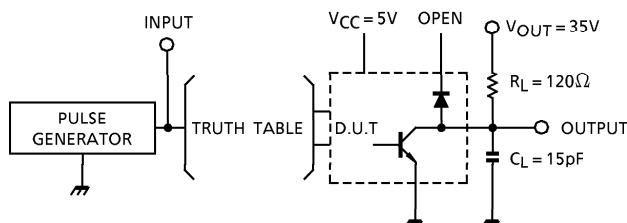
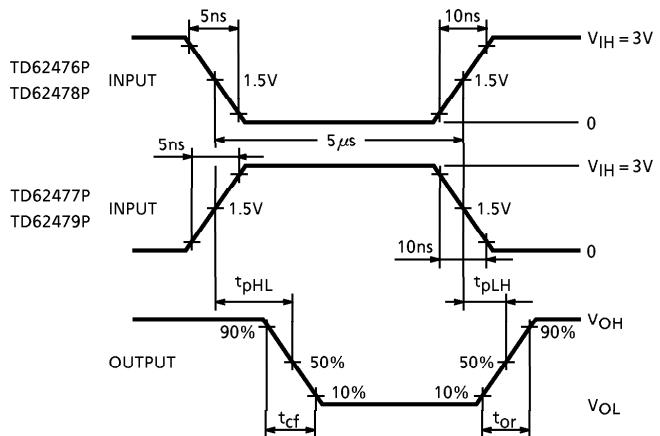
CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION		MIN.	TYP.	MAX.	UNIT			
Input Voltage		"H" Level	V <sub>IH</sub>	—		2.0	—	—	V			
		"L" Level	V <sub>IL</sub>	—		—	—	0.8				
Output Current	"H" Level	I <sub>OH</sub>	2	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.8V, V_{OH} = 35V$		—	—	10	$\mu A$			
Output Voltage		V <sub>OL</sub>	3	$V_{CC} = 4.5V$	I <sub>OUT</sub> = 100mA	—	0.15	0.30	V			
				$V_{IH} = 2.0V$	I <sub>OUT</sub> = 200mA	—	0.28	0.45				
				$V_{IL} = 0.8V$	I <sub>OUT</sub> = 300mA	—	0.45	0.60				
Input Current		"H" Level	I <sub>IH</sub>	$V_{CC} = 5.5V, V_{IN} = 5.5V$		—	—	10	$\mu A$			
		"L" Level	I <sub>IL</sub>	$V_{CC} = 5.5V, V_{IN} = 0.4V$		—	-0.26	-0.4	mA			
				—		—	-0.52	-0.8				
Clamp Diode Reverse Current			I <sub>R</sub>	6	$V_{CC} = 4.5V, V_R = 35V$		—	—	$\mu A$			
Clamp Diode Forward Voltage			V <sub>F</sub>	7	$V_{CC} = 4.5V, I_F = 300mA$		—	1.5	1.75	V		
Supply Current	Output Off	TD62476P	I <sub>CCH</sub>	5	$V_{CC} = 5.5V$	V <sub>IN</sub> = 5V	—	8.4	14	mA		
		TD62477P				V <sub>IN</sub> = 0V	—	0.6	0.85			
		TD62478P				V <sub>IN</sub> = 5V	—	9	14			
		TD62479P				V <sub>IN</sub> = 0V	—	1.1	1.8			
	Output On	TD62476P	I <sub>CCL</sub>			V <sub>IN</sub> = 5V	—	38	55			
		TD62477P				V <sub>IN</sub> = 0V	—	36	53			
		TD62478P				V <sub>IN</sub> = 5V	—	39	56			
		TD62479P				V <sub>IN</sub> = 0V	—	36	63			

SWITCHING CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	CONDITION		MIN.	TYP.	MAX.	UNIT
Propagation Delay Time		t <sub>pLH</sub>	—	$C_L = 15pF, R_L = 120\Omega$		—	0.7	—	$\mu s$
		t <sub>pHL</sub>	—			—	0.2	—	

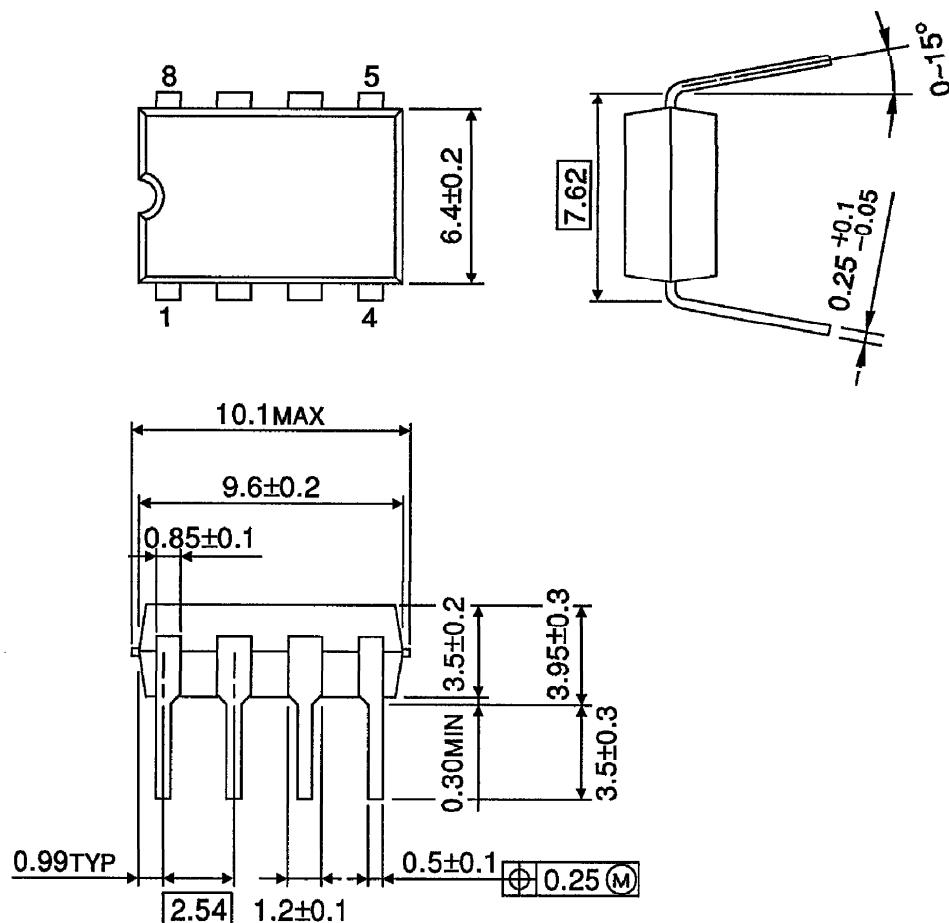
**TEST CIRCUIT**1.  $V_{IH}, V_{IL}$ 3.  $V_{OL}$ 5.  $I_{IL}, I_{CCH}$ 7.  $V_F$ 2.  $I_{OH}$ 4.  $I_{IH}, I_{CCL}$ 6.  $I_R$ **PRECAUTIONS for USING**

Utmost care is necessary in the design of the output line,  $V_{CC}$ , COMMON and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

**TEST CIRCUIT OF SWITCHING CHARACTERISTIC****TEST WAVEFORM**

**OUTLINE DRAWING**  
DIP8-P-300-2.54

Unit : mm



Weight : 0.45g (Typ.)